CLAIMS~~:~~

1. A non-aqueous cleaning composition for micro-electronics applications ~~comprising~~consisting essentially of:

about 0.~~01~~2% to about 1.5~~.0~~ % by weight of a fluoride activating agent, wherein said fluoride activating agent is hydrogen fluoride, Fluoroboric acid, or a combination of hydrogen fluoride and Fluoroboric acid,

about 1.0~~.01~~% to ~~5.0~~about 2.8% by weight of at least one oxidizer, wherein said one oxidizer is ~~selected from the group consisting of~~ nitric acid~~,~~ or a combination of nitric acid and sulfuric acid, ~~sulfonic acid, periodic acid, ammonium persulfate, peroxymonosulfuric acid, perborates, percarbonates, persulfates, ozone and ozonides, 80.00~~and

about 93.2% to ~~99.90~~about 98.8% by weight of an anhydrous organic solvent, wherein said anhydrous organic solvent is sulfolane,

wherein said cleaning composition has a pH equal to 5.~~0~~5 or less, and wherein ~~and wherein~~ said composition is in the absence of hydrogen peroxide.

2. The non-aqueous cleaning composition according to claim 1~~,~~ wherein said cleaning composition also has etch capabilities.

3. The non-aqueous cleaning composition according to claim 1~~,~~ wherein said cleaning composition is compatible with tungsten and low-~~K~~κ dielectric substrates.

~~4. The non-aqueous cleaning composition according to claim 1, comprising 0.05% to 1.00 % by weight of a fluoride activating agent, 0.01% to 5.00% by weight of at least one oxidizer, and 85.00% to 99.90% by weight of an anhydrous organic solvent.~~

~~5. The non-aqueous cleaning composition according to claim 1, comprising 0.10% to 0.50 % by weight of a fluoride activating agent, 0.01% to 2.00% by weight of at least one oxidizer, and 90.00% to 99.00% by weight of an anhydrous organic solvent.~~

~~6. The non-aqueous cleaning composition according to claim 1, further comprising a co-solvent.~~

~~7. The non-aqueous cleaning composition according to claim 1, further comprising one or more ingredient selected from the group comprising a pH-adjusting agent, an amine, acids, a corrosion control agent, and a surfactant.~~

~~8. The non-aqueous cleaning composition according to claim 1, wherein said fluoride activating agent is selected from the group of hydrogen fluoride, ammonium fluoride, potassium fluoride, alkali metal fluorides, tetraalkyl -ammonium fluoride, fluoroboric acid, ammonium tetrafluoroborate, alkali metal tetrafluoroborate, tetraalkylammonium tetrafluoroborate, and~~

~~trimethyloxonium tetrafluoroborate.~~

~~9.~~4. A method of cleaning a mirco-electronic substrate comprising contacting said micro-electronic substrate with a cleaning composition ~~comprising 0.01% to 5.0 % by weight of a fluoride activating agent, 0.01% to 5.0% by weight of at least one oxidizer, wherein said one oxidizer is selected from the group consisting of nitric acid, sulfuric acid, sulfonic acid, periodic acid, ammonium persulfate, peroxymonosulfuric acid, perborates, percarbonates, persulfates, ozone and ozonides, 80.00% to 99.90% by weight of an anhydrous organic solvent, wherein said anhydrous organic solvent is sulfolane, wherein said cleaning composition has a pH equal to 5.0 or less, and wherein and wherein said composition is in the absence of hydrogen peroxide.~~consisting essentially of:

~~10. A non-aqueous cleaning composition for micro-electronics applications comprising~~about 0.~~01~~2% to about 1.5~~.0~~ % by weight of a fluoride activating agent ~~in the form~~, wherein said fluoride activating agent is hydrogen fluoride, Fluoroboric acid, or a combination of ~~HF or HBF4, 0.01~~hydrogen fluoride and Fluoroboric acid,

about 1.0% to ~~20.00~~about 2.8% by weight of at least one oxidizer ~~comprising~~ , wherein said one oxidizer is nitric acid~~, 80.00~~ or a combination of nitric acid and sulfuric, and

about 93.2% to ~~99.90~~about 98.8% by weight of an anhydrous organic solvent, wherein said anhydrous organic solvent is sulfolane,

wherein said cleaning composition has a pH equal to 5.~~0~~5 or less, and wherein said ~~oxidizer~~composition is ~~not~~in the absence of hydrogen peroxide.

~~11. The non-aqueous cleaning composition according to claim 10, wherein said cleaning composition also has etch capabilities.~~

~~12. The non-aqueous cleaning composition according to claim 10, wherein said cleaning composition is compatible with tungsten and low-K dielectric substrates.~~

~~13. The non-aqueous cleaning composition according to claim 10, comprising 0.05% to 1.00 % by weight of a fluoride activating agent, 0.01% to 5.00% by weight of at least one oxidizer, and 85.00% to 99.90% by weight of an anhydrous organic solvent.~~

~~14. The non-aqueous cleaning composition according to claim 10, comprising 0.10% to 0.50 % by weight of the fluoride activating agent, 0.01% to 2.00% by weight of the at least one oxidizer, and 90.00% to 99.00% by weight of the anhydrous organic solvent.~~

~~15. The non-aqueous cleaning composition according to claim 10, further comprising a co-solvent.~~

~~16. The non-aqueous cleaning composition according to claim 10, further comprising one or more ingredient selected from the group comprising a pH-adjusting agent, an amine, acids, a corrosion control agent, and a surfactant.~~

~~17. The non-aqueous cleaning composition according to claim 10, wherein said anhydrous organic solvent is selected from the group of sulfones, sulfides, carbonates, alcohols, glycols and amides.~~

~~18. The non-aqueous cleaning composition according to claim 17, wherein said anhydrous organic solvent is sulfolane.~~

~~19. A method of cleaning a mirco-electronic substrate comprising contacting said micro-electronic substrate with a cleaning composition comprising 0.01% to 5.0 % by weight of a fluoride activating agent, 0.01% to 5.0 % by weight of a fluoride activating agent in the form of HF or HBF4, 0.01% to 20.00% by weight of at least one oxidizer comprising nitric acid, 80.00% to 99.90% by weight of an anhydrous organic solvent, wherein said cleaning composition has a pH equal to 5.0 or less, and wherein said oxidizer is not hydrogen peroxide.~~